

5 laser annealing the amorphous semiconductor material to form a  
6 single crystalline semiconductor layer containing germanium; and  
7 doping the single crystalline semiconductor layer and the substrate  
8 at a source location and a drain location to form a source region and a drain  
9 region, whereby a channel region between the source region and the drain  
10 region includes a thin semiconductor germanium region.

B1  
copy  
sub  
B2

1 8. (Amended) The method of claim 1, wherein the amorphous  
2 semiconductor material includes silicon germanium.

B2

1 9. (Amended) The method of claim 7, wherein the amorphous  
2 semiconductor material includes silicon germanium.

B3  
sub  
B2

1 11. (Amended) The method of claim 1, further comprising  
2 providing a second amorphous semiconductor material above the  
3 amorphous semiconductor material including germanium before the laser  
4 annealing step, wherein the laser annealing step forms a second single  
5 crystalline semiconductor layer from the second amorphous semiconductor  
6 material; and  
7 siliciding the source region and the drain region to form a silicided  
8 layer wherein the depth of the silicided layer is deeper than the second single  
9 crystalline semiconductor layer.